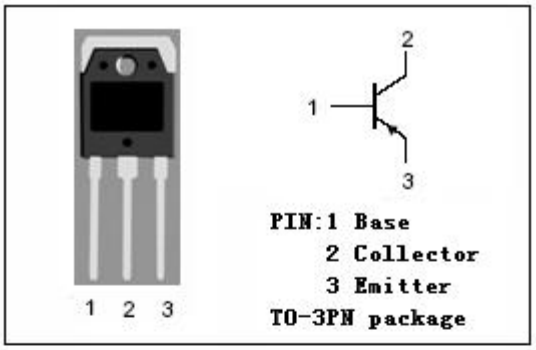
isc Silicon PNP Power Transistor 2SB828

DESCRIPTION

- High Collector Current:: I_C= -12A
- Low Collector Saturation Voltage
  : $V_{CE(sat)}$= -0.5V(Max)@I_C= -6A
- Wide Area of Safe Operation
- Complement to Type 2SD1064
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

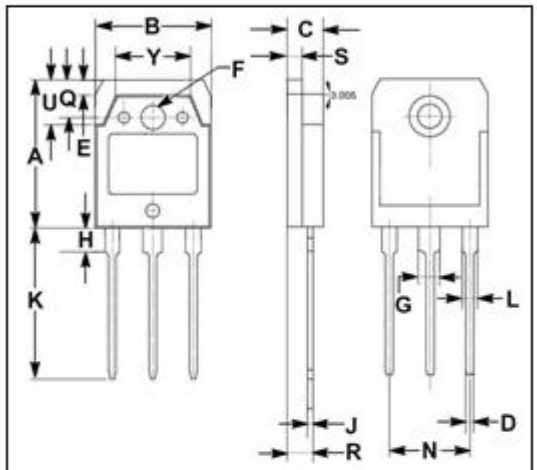


APPLICATIONS

- Designed for relay drivers,high-speed inverters,converters, and other gereral high-current switching applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-50	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current-Continuous	-12	A
I_{CM}	Collector Current-Peak	-17	A
P_C	Total Power Dissipation @ T_C=25℃	80	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃



DIM	mm MIN	MAX
A	19.60	20.10
B	15.50	15.70
C	4.70	4.90
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.90	3.20
H	3.20	3.40
J	0.595	0.605
K	20.00	20.70
L	1.90	2.20
N	10.89	10.91
Q	4.90	5.10
R	3.35	3.45
S	1.995	2.100
U	5.90	6.10
Y	9.90	10.10

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= -1mA ; R_{BE}= ∞	-50			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C= -1mA ; I_E= 0	-60			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= -1mA ; I_C= 0	-6			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -6A; I_B= -0.3A			-0.5	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -40V; I_E= 0			-0.1	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -4V; I_C= 0			-0.1	mA
h_{FE-1}	DC Current Gain	I_C= -1A; V_{CE}= -2V	70		280	
h_{FE-2}	DC Current Gain	I_C= -5A; V_{CE}= -2V	30			

◆ **h_{FE-1} Classifications**

Q	R	S
70-140	100-200	140-280